

## OptiMOS™-T2 Power-Transistor



### Features

- N-channel Logic Level - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

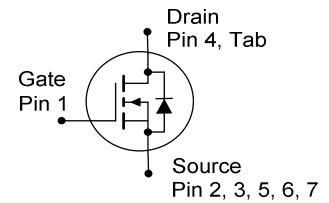
### Product Summary

|              |     |    |
|--------------|-----|----|
| $V_{DS}$     | 40  | V  |
| $R_{DS(on)}$ | 1.5 | mΩ |
| $I_D$        | 160 | A  |

PG-TO263-7-3



| Type            | Package      | Marking |
|-----------------|--------------|---------|
| IPB160N04S4L-H1 | PG-TO263-7-3 | 4N04LH1 |



Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol         | Conditions                                          | Value        | Unit |
|-------------------------------------|----------------|-----------------------------------------------------|--------------|------|
| Continuous drain current            | $I_D$          | $T_C=25\text{ °C}$ , $V_{GS}=10\text{ V}^{(1)}$     | 160          | A    |
|                                     |                | $T_C=100\text{ °C}$ ,<br>$V_{GS}=10\text{ V}^{(2)}$ | 160          |      |
| Pulsed drain current <sup>(2)</sup> | $I_{D,pulse}$  | $T_C=25\text{ °C}$                                  | 640          |      |
| Avalanche energy, single pulse      | $E_{AS}$       | $I_D=80\text{ A}$                                   | 400          | mJ   |
| Avalanche current, single pulse     | $I_{AS}$       | -                                                   | 160          | A    |
| Gate source voltage                 | $V_{GS}$       | -                                                   | +20/-16      | V    |
| Power dissipation                   | $P_{tot}$      | $T_C=25\text{ °C}$                                  | 167          | W    |
| Operating and storage temperature   | $T_j, T_{stg}$ | -                                                   | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1 | -              | -                                                   | 55/175/56    |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics<sup>2)</sup>**

|                                     |            |   |   |   |     |     |
|-------------------------------------|------------|---|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ | - | - | - | 0.9 | K/W |
|-------------------------------------|------------|---|---|---|-----|-----|

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |                                                                |     |      |     |               |
|----------------------------------|---------------|----------------------------------------------------------------|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                           | 40  | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=110\text{ }\mu\text{A}$                    | 1.2 | 1.7  | 2.2 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=40\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$      | -   | 0.05 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=18\text{ V}, V_{GS}=0\text{ V}, T_j=85\text{ °C}^{2)}$ | -   | 1    | 20  |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                        | -   | -    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=50\text{ A}$                         | -   | 1.6  | 2.0 | m $\Omega$    |
|                                  |               | $V_{GS}=10\text{ V}, I_D=100\text{ A}$                         | -   | 1.2  | 1.5 |               |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Dynamic characteristics<sup>2)</sup>

|                              |              |                                                                                  |   |       |       |    |
|------------------------------|--------------|----------------------------------------------------------------------------------|---|-------|-------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$<br>$f=1\text{ MHz}$                     | - | 11500 | 14950 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                  | - | 1920  | 2500  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                  | - | 100   | 230   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=20\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=160\text{ A}, R_G=3.5\ \Omega$ | - | 16    | -     | ns |
| Rise time                    | $t_r$        |                                                                                  | - | 20    | -     |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                  | - | 70    | -     |    |
| Fall time                    | $t_f$        |                                                                                  | - | 65    | -     |    |

### Gate Charge Characteristics<sup>2)</sup>

|                       |               |                                                                             |   |     |     |    |
|-----------------------|---------------|-----------------------------------------------------------------------------|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=32\text{ V}, I_D=160\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 34  | 44  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                             | - | 16  | 37  |    |
| Gate charge total     | $Q_g$         |                                                                             | - | 146 | 190 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                             | - | 3.0 | -   | V  |

### Reverse Diode

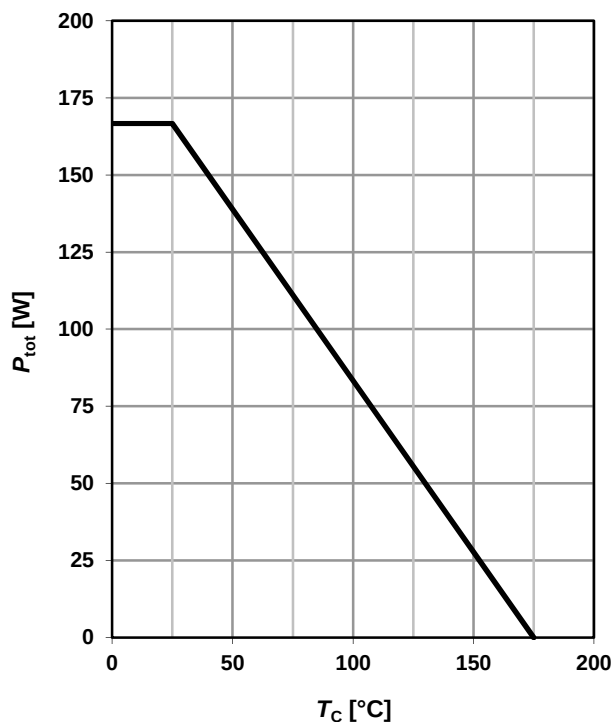
|                                                |               |                                                                           |   |     |     |    |
|------------------------------------------------|---------------|---------------------------------------------------------------------------|---|-----|-----|----|
| Diode continuous forward current <sup>2)</sup> | $I_S$         | $T_C=25\text{ °C}$                                                        | - | -   | 160 | A  |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ |                                                                           | - | -   | 640 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=100\text{ A},$<br>$T_j=25\text{ °C}$              | - | 0.9 | 1.3 | V  |
| Reverse recovery time <sup>2)</sup>            | $t_{rr}$      | $V_R=20\text{ V}, I_F=50\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 60  | -   | ns |
| Reverse recovery charge <sup>2)</sup>          | $Q_{rr}$      |                                                                           | - | 80  | -   | nC |

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 0.9\text{ K/W}$  the chip is able to carry 250A at 25°C.

<sup>2)</sup> Defined by design. Not subject to production test.

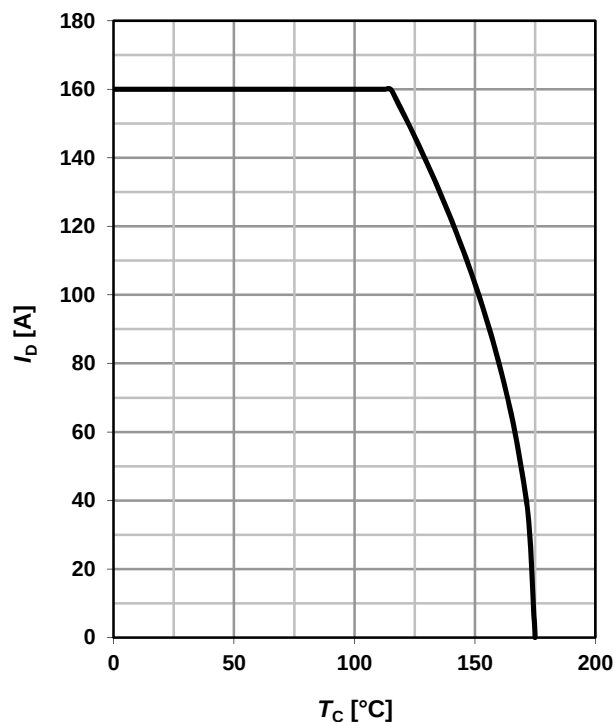
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 2 Drain current

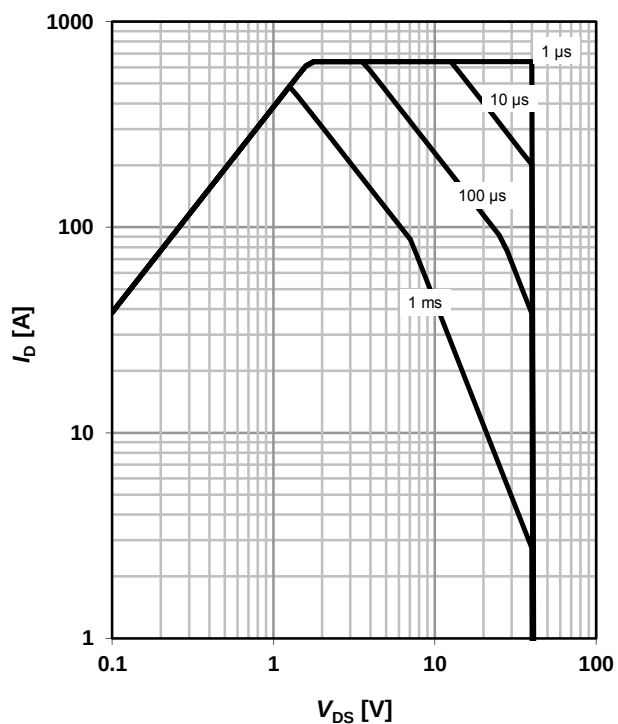
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

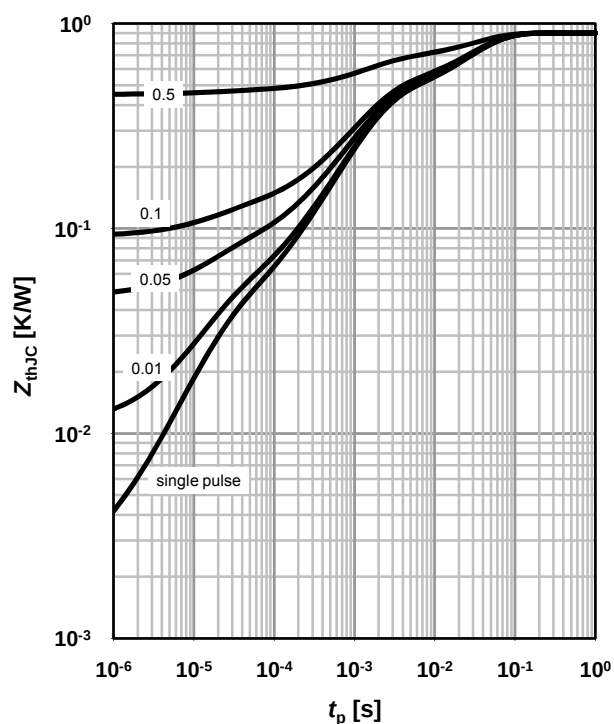
parameter:  $t_p$



### 4 Max. transient thermal impedance

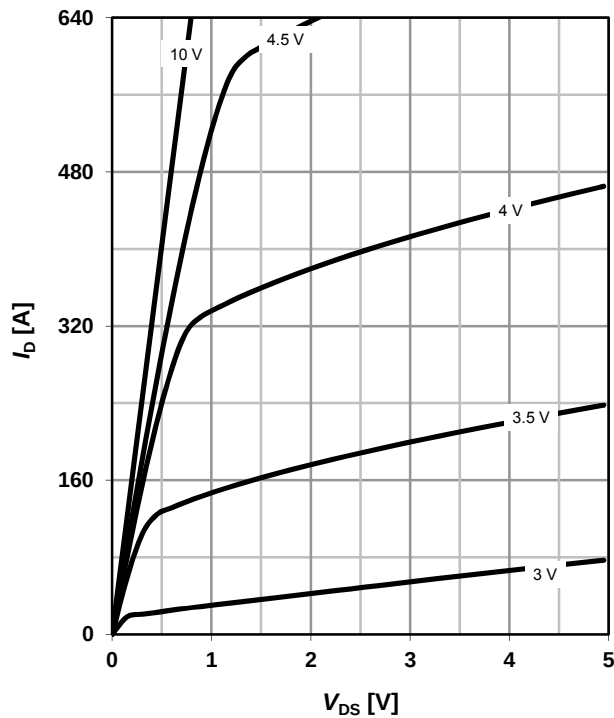
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



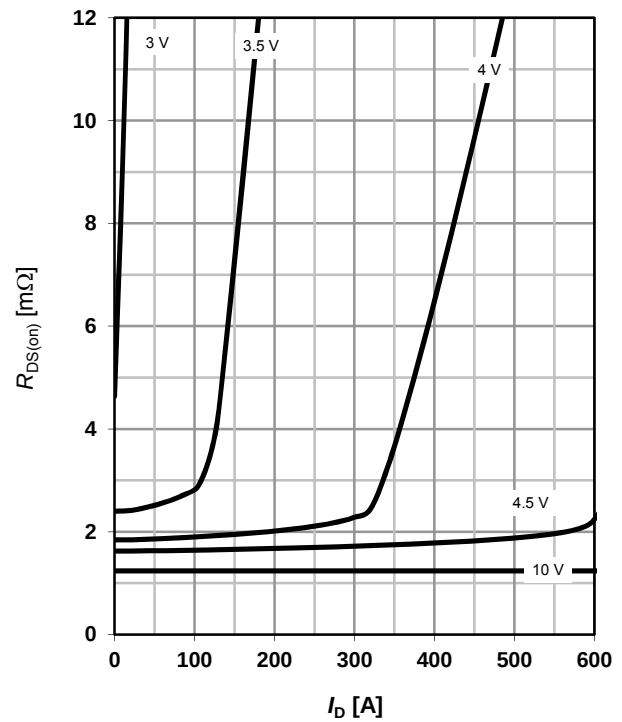
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


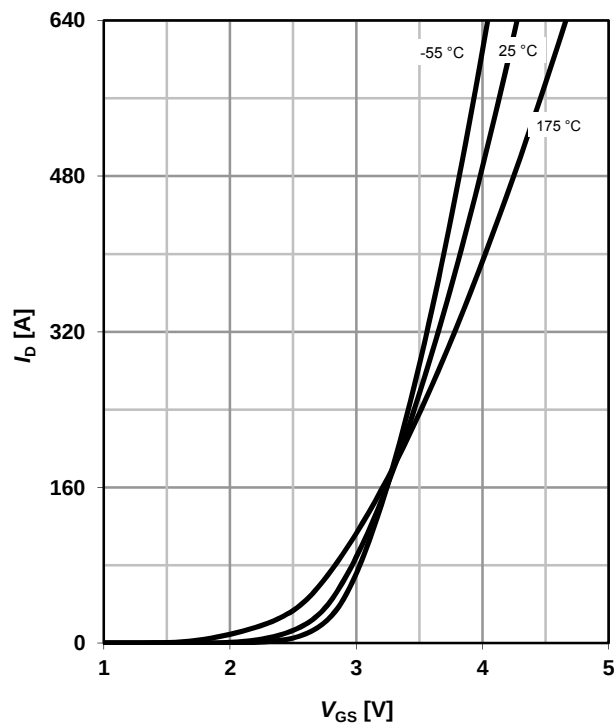
### 6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

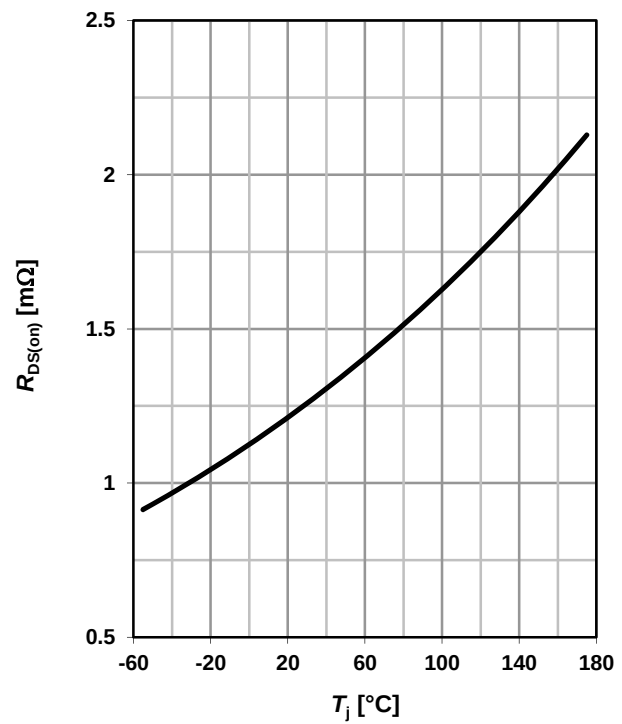
parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{ V}$ 

parameter:  $T_j$ 


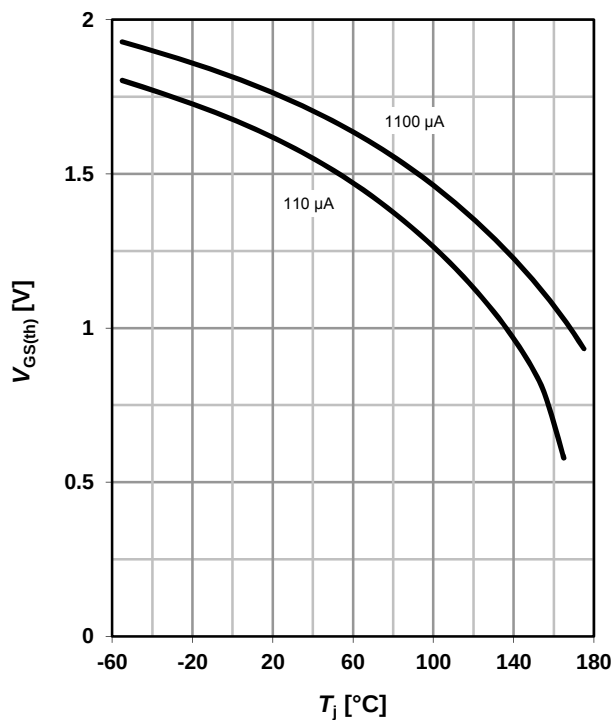
### 8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 100\text{ A}; V_{GS} = 10\text{ V}$ 


## 9 Typ. gate threshold voltage

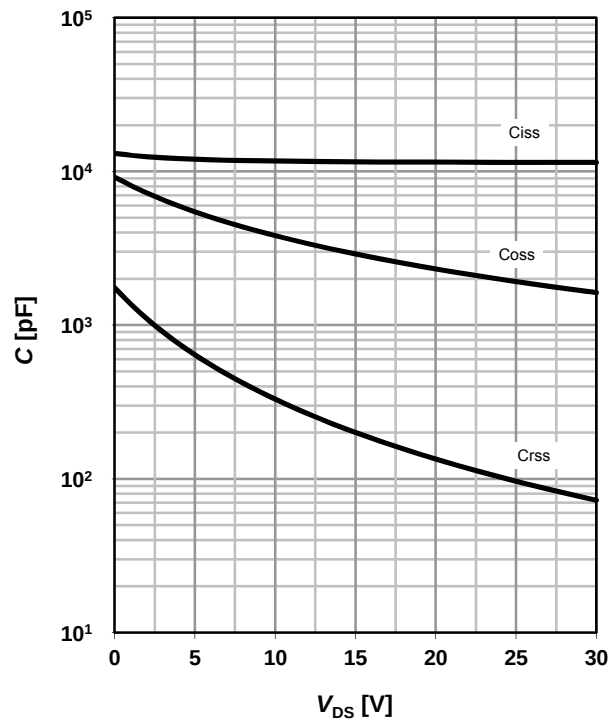
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



## 10 Typ. capacitances

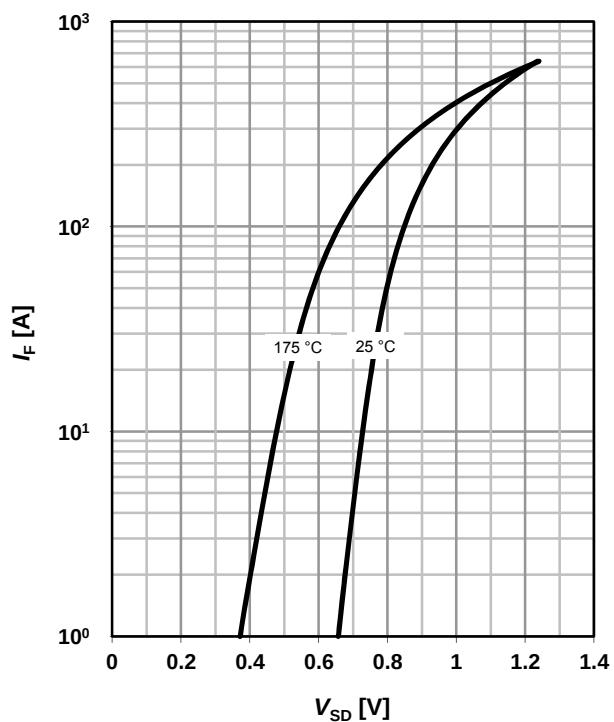
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$



## 11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

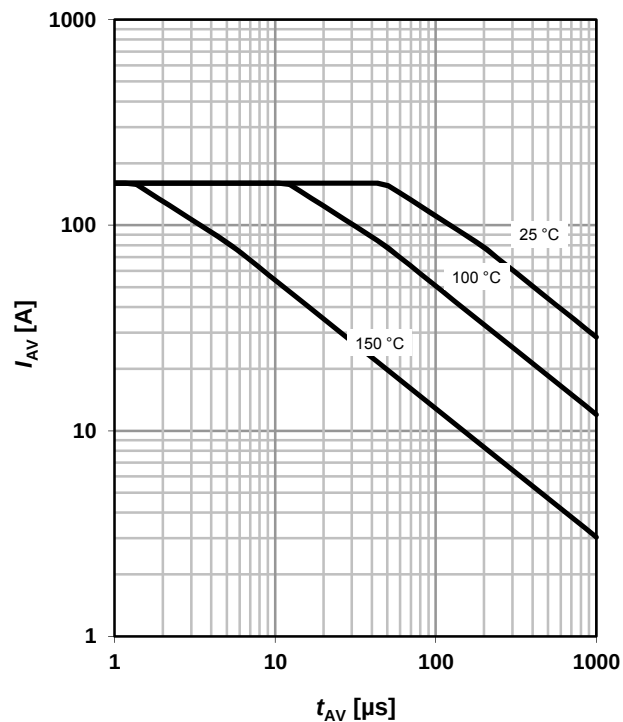
parameter:  $T_j$



## 12 Typ. avalanche characteristics

$$I_{AS} = f(t_{AV})$$

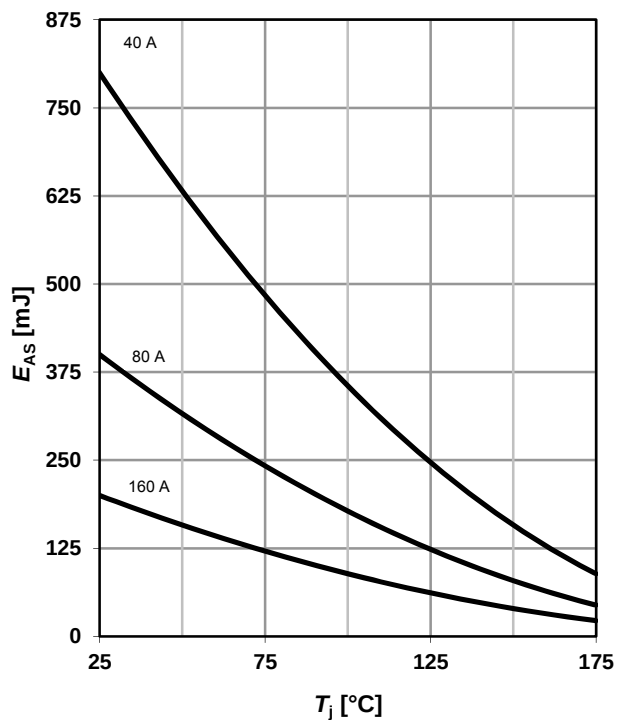
parameter:  $T_{j(start)}$



### 13 Typical avalanche energy

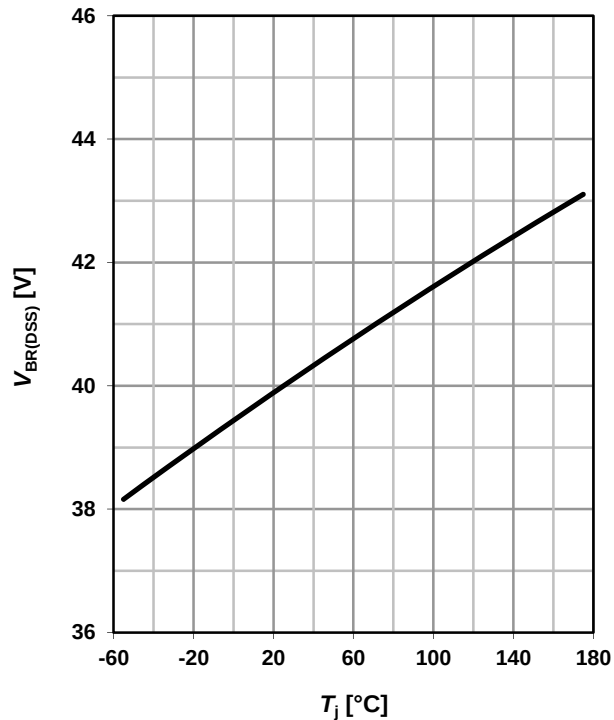
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

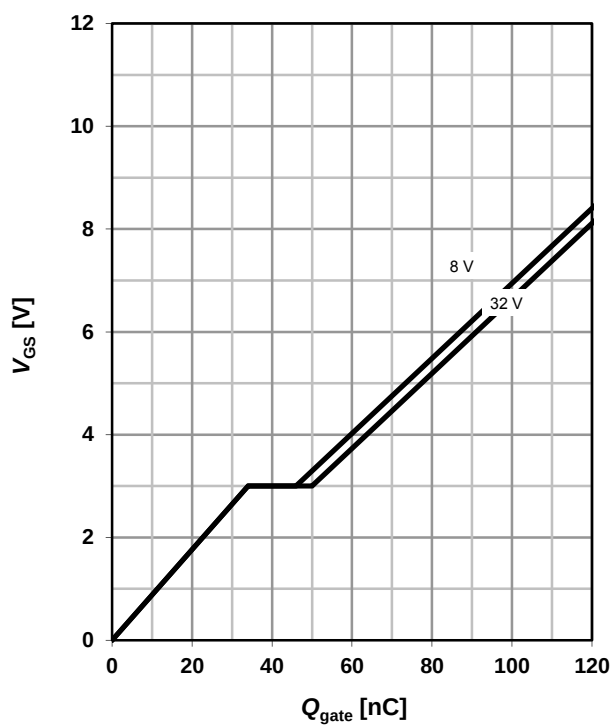
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



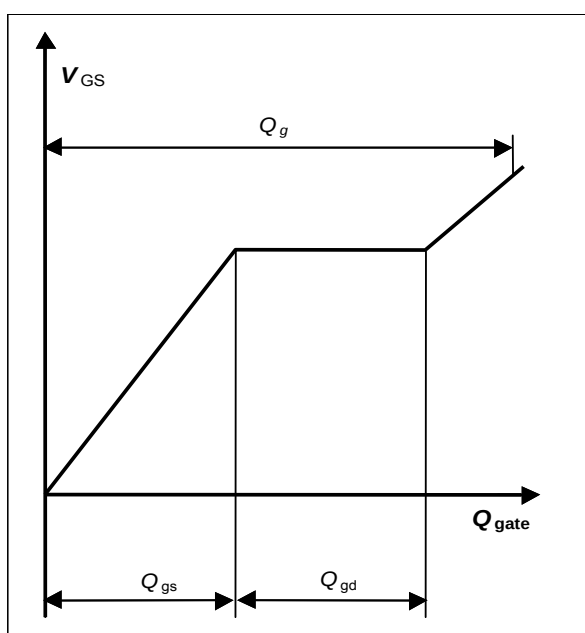
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 160 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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## Revision History

| Version      | Date       | Changes    |
|--------------|------------|------------|
| Revision 1.0 | 27.05.2013 | Data Sheet |

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

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- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
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- Работу по проектам и поставку образцов.
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- Наличие сертификата ISO.

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Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
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